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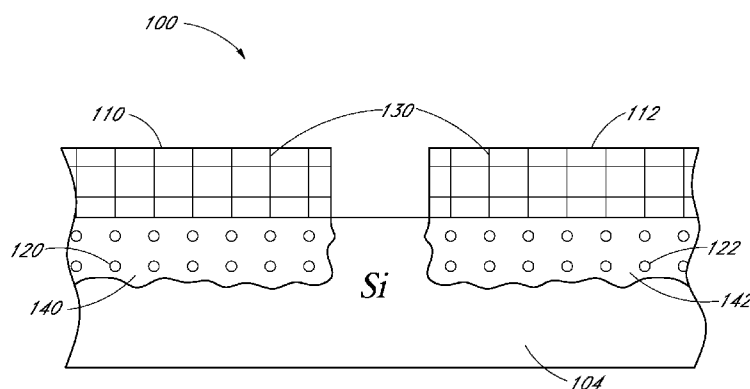
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**FIG. 5**

(57) Abstract: A method of manufacturing solar cells is disclosed. The method comprises depositing an etch-resistant dopant material on a silicon substrate, the etch-resistant dopant material comprising a dopant source, forming a cross-linked matrix in the etch-resistant dopant material using a non-thermal cure of the etch-resistant dopant material, and heating the silicon substrate and the etch-resistant dopant material to a temperature sufficient to cause the dopant source to diffuse into the silicon substrate.